



Features:

- RoHS Compliant
- 125 Watts
- DC 4.0 GHz
- AIN Ceramic
- Non-Nichrome Resistive
 Element
- Low VSWR
- 100% Tested
- Small Size

Outline Drawing

Description

The A125N50X4 is high performance Aluminum Nirtride (AIN) chip termination intended as an alternative to Beryllium Oxide (BeO). The termination is well suited to all cellular frequency bands such as; AMPS, GSM, DCS, PCS, PHS and UMTS. The high power handling makes the part ideal for terminating circulators and for use in power combiners. The termination is also RoHS compliant!

Model A125N50X4

Chip Termination

125 Watts, 50 Ω

General Specifications

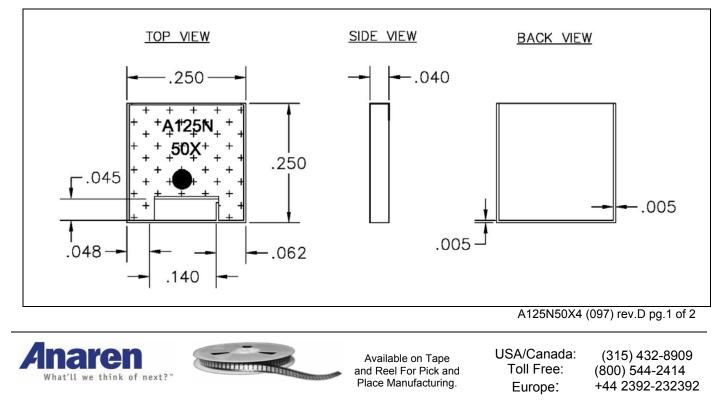
ROHS Compliant

Resistive Element	Thick film
Substrate	AIN Ceramic
Terminal Finish	Matte Tin over Nickel Barrier
Operating Temperature	-55 to +150°C (see de rating chart)
Tolerance is ± 0.010 ", unless otherwise specified. Designed to meet of exceed applicable portions of MIL-E-5400. All dimensions in inches.	

Electrical Specifications

Resistance Value:	50 Ohms, ± 2%
Power:	125 Watts
Frequency Range:	DC – 4.0 GHz
Return Loss	> 26 dB to 2.7 GHz
	> 20 dB to 4.0 GHz

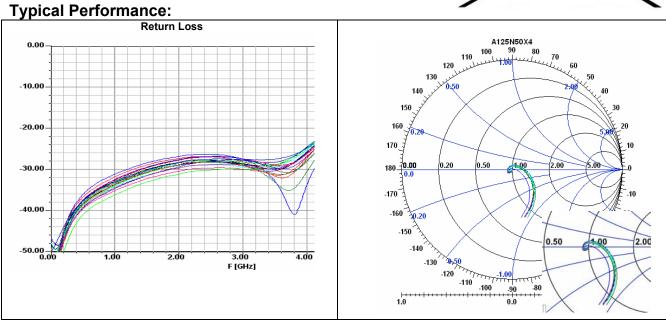
Specification based on unit properly installed using suggested mounting instructions and a 50 ohm nominal impedance. **Specifications subject to change.**



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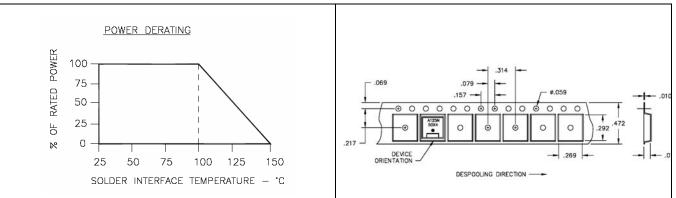


<u>_____RF Power</u>

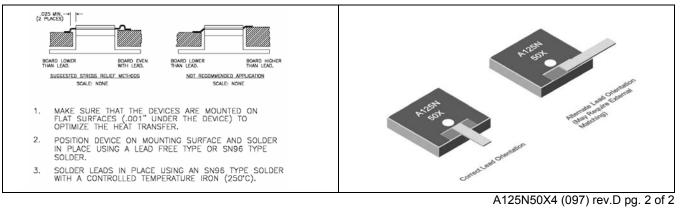




Tape & Reel:



Mounting Footprint and Procedure:



USA/Canada: Toll Free: Europe: (315) 432-8909 (800) 544-2414 +44 2392-232392

Available on Tape and Reel For Pick and Place Manufacturing.

